

# Ultraviolet photodetector composed of ZnO nanosheets/Cu<sub>2</sub>O heterostructure fabricated by hydrothermal process

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A highly sensitive ultraviolet detector (UV) sensor composed of ZnO nanosheets/Cu<sub>2</sub>O heterostructure was fabricated. It composed of two dimensional ZnO nanosheets and Cu<sub>2</sub>O film. The photoresponse results showed that the fabricated UV detector were sensitive to UV light illumination with good stability and reproducibility. The high UV response performance can be attributed to heterojunction formation and large surface area provided by ZnO sheets-like structures. The results indicated the suitability of the simple and low-cost ZnO nanosheets/Cu<sub>2</sub>O heterojunction device for optoelectronic applications.

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## 1. Introduction

With a direct wide band gap (3.37 eV) and relatively large exciton binding energy of (60 meV) ZnO has been widely investigated for many optoelectronic, chemical and biosensing applications [1-10]. Likewise, cuprous oxide (Cu<sub>2</sub>O) is another important metal oxide material that has been substantially explored for various fields of applications [11-14]. Till now, the Cu<sub>2</sub>O/ZnO heterojunctions that were achieved by direct growth of Cu<sub>2</sub>O on ZnO have been demonstrated [15-16]. However, these methods usually need high temperature, high pressure, high cost, especially high energy consumption. Therefore, developing a straightforward, low cost and

low energy consumption way to synthesize large-area Cu<sub>2</sub>O/ZnO heterojunction is a very important.

Meanwhile, the fabrication of ZnO/Cu<sub>2</sub>O heterojunction has attracted optoelectronic and sensor applications. Because it can obtain excellent optical and electrical properties of ZnO and high absorption of Cu<sub>2</sub>O in visible region. In recent years, the formation of nanostructured Cu<sub>2</sub>O and ZnO by hydrothermal reaction has been attracted considerable attention due to its simplicity and large-scale growth ability [17]. However, it is also not easy to grow ZnO/Cu<sub>2</sub>O heterostructure just by using single fabrication technique.

In this study, we reported a novel heterojunction structure composed of ZnO nanosheets and Cu<sub>2</sub>O film, which was fabricated by a simple aqueous method. The heterostructure exhibited a prominent performance for UV detection response. It can be attributed to the increased surface area by the ZnO nanosheets and local p-n junction areas. The results indicated the suitability of low-cost Cu<sub>2</sub>O/ZnO heterojunction device for optoelectronic applications. Furthermore, it will provide a facile route for large area growth Cu<sub>2</sub>O/ZnO heterostructure for low cost UV detector applications.

## 2. Experimental

Cu<sub>2</sub>O film was firstly prepared on pre-cleaned indium tin oxide (ITO) glass plate by two-step growth method. The ITO glass substrate was seeded via spin coating with 0.03M Cu (CH<sub>3</sub>COO)<sub>2</sub>·2H<sub>2</sub>O solution with alcohol as solvent and then annealed at 200°C to achieve good adhesion between the seeding layer and the substrate. In a typical experiment 0.01 M aqueous solution of Cu (CH<sub>3</sub>COO)<sub>2</sub>·2H<sub>2</sub>O and C<sub>6</sub>H<sub>12</sub>N<sub>4</sub> was prepared. The ITO glass was put into the above solution at 90 for 5 h. For the growth of ZnO nanosheets structures, the Cu<sub>2</sub>O/ITO substrate was seeded via spin-coating by using zinc acetate solution with alcohol as solvent, then annealing at 200°C for 30min. Then, 0.03M (Zn(CH<sub>3</sub>COO)<sub>2</sub>) was prepared. And it was dissolved in alcohol at room temperature. Finally, the seeded Cu<sub>2</sub>O/ITO was immersed into the alcohol reaction solution, and the react temperature was kept at 70°C with 5 h hours.

Structural characteristics of as-grown heterostructures were investigated using X-ray diffraction (XRD). The morphology of the as-deposited material was examined using scanning electron microscopy (FE-SEM, Hitachi S-4800). The current voltage characteristics of the sample were measured using a Keithley 2400 voltage source instrument. The device performance was characterized by current-voltage (I-V) characteristics and time photoresponse measurement was carried out by switching the light from a portable UV lamp ( $\lambda = 365 \text{ nm}$ ,  $30 \text{ mW/cm}^2$ ) on and off.

The distance between the sample and the UV lamp was fixed.

## 3. Results

Fig. 1 showed the XRD patterns of as-grown ZnO/Cu<sub>2</sub>O heterojunction structures. All the peaks in the patterns correspond to the hexagonal Wurtzite and cubic type structures of the ZnO and Cu<sub>2</sub>O crystallites, respectively. The peaks at 43.9°, 64.4° and 77.4° are originated from (200), (220) and (220) lattice planes of face centered cubic Cu<sub>2</sub>O phase [JCPDS card no. 34-1354]. Meanwhile, the peaks observed 31.8°, 34.6°, 36.5° and 47.8° which corresponded to the planes (100), (002), (101) and (102) of hexagonal wurtzite ZnO phase (JCPDS 36-1454). No additional peaks related to other phases such as Zn, Zn(OH)<sub>2</sub> were detected suggesting that the grown ZnO nanostructures are of high purity.

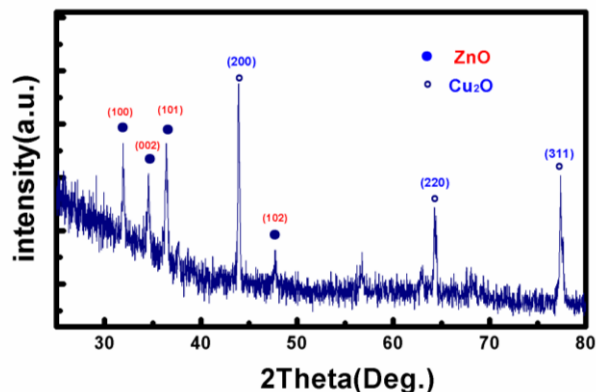


Fig. 1. The XRD patterns of as-grown Cu<sub>2</sub>O/ZnO heterojunction structures

Fig. 2 (a) showed the SEM image of the surface morphology of the as-grown Cu<sub>2</sub>O film with top view. The film shows grain-like morphology. And it shows densely packed and uniform size crystallites. Meanwhile, it can be seen that the film has a quite uniform surface and the average grain size is about 30 nm. Fig. 2 (b) and (c) displayed the SEM images of ZnO nanosheets prepared on Cu<sub>2</sub>O layer with different magnifications. It can be seen that the substrate is covered by hexagonal sheets with almost uniform diameter in a large scale. From the SEM images, we can also observe that these sheets are

vertical to the Cu<sub>2</sub>O layer. Fig. 2 (d) depicted the cross-sectional SEM of as-grown Cu<sub>2</sub>O/ZnO nanosheets heterostructure. It can be seen that as-synthesized ZnO nanosheets merged with each other to form densely packed film, and the thickness is around 150 nm.

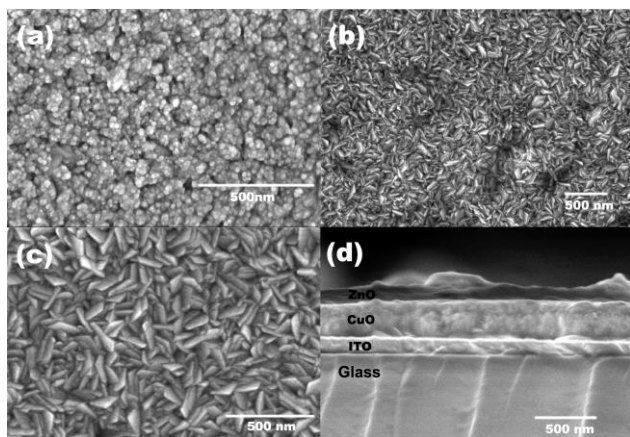


Fig. 2. (a) SEM image of the Cu<sub>2</sub>O film grown on ITO/glass substrate. SEM images of Cu<sub>2</sub>O/ZnO heterostructure structures with different magnifications. (b) low magnification (c) high magnification. (d) The cross-sectional view of Cu<sub>2</sub>O/ZnO heterostructure structure

The schematic structure of the Cu<sub>2</sub>O/ZnO nanosheets heterostructure photodetector was shown in the Fig.3. The ITO film was used to act as top electrodes to increase the contacting area on the ZnO nanostructures. Then, the as-grown Cu<sub>2</sub>O/ZnO nanosheets heterostructure was placed on the prepared ITO/glass substrate. The tip of Cu<sub>2</sub>O/ZnO nanosheets heterostructure was directly contacted with the ITO/glass substrate. The UV response of the devices was characterized by a portable UV lamp at room temperature.

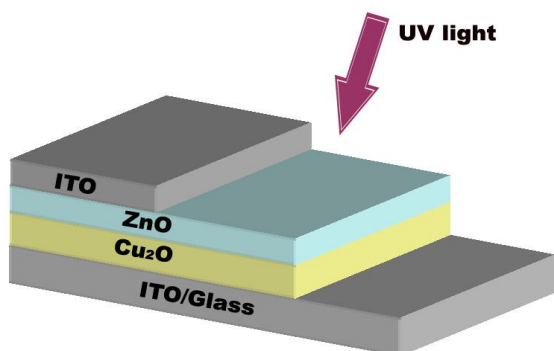


Fig. 3. The schematic diagram of Cu<sub>2</sub>O/ZnO heterostructure device structures

The I-V characteristics of the photodetector based on ZnO nanosheets/Cu<sub>2</sub>O heterostructure under dark and UV illumination are shown in Fig.4. The I-V curve was measured with bias from -5 to 5 V at room temperature in ambient condition. Clear rectifying behavior can be observed for the sample with and without UV illumination. The current of ZnO nanosheets/Cu<sub>2</sub>O heterostructure was increased from  $3.4 \times 10^{-7}$  A to  $7.2 \times 10^{-6}$  A under UV illumination with an applied voltage of 3 V.

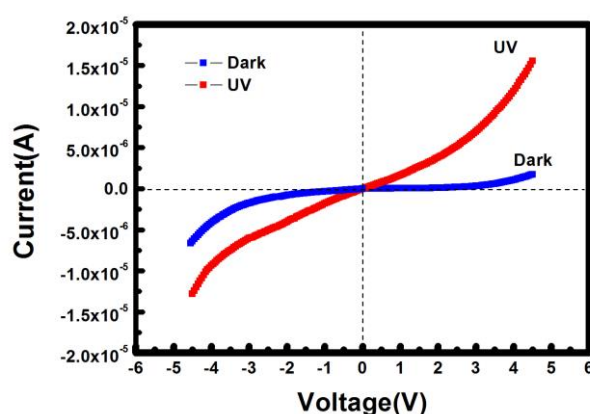


Fig. 4. Current-voltage characteristics of Cu<sub>2</sub>O/ZnO heterostructure under dark and illuminated conditions

The repeatability and response speed of the Cu<sub>2</sub>O/ZnO nanosheets heterostructure UV detector were measured. Fig. 5 showed the time-dependent response of the ZnO nanosheets/Cu<sub>2</sub>O heterostructure structure. The time-resolved photocurrent was measured under 3V bias with multiple UV on/off cycles, in which both the UV light turn-on and turn-off times of the UV light were 30 s. It can be seen that the heterostructure exhibits a nearly identical and repeatable response after multiple illumination cycles. Meanwhile, the photocurrent increases very rapidly upon exposure to UV radiation, stays essentially constant during the UV light exposure, and decays very fast when UV light is turned off.

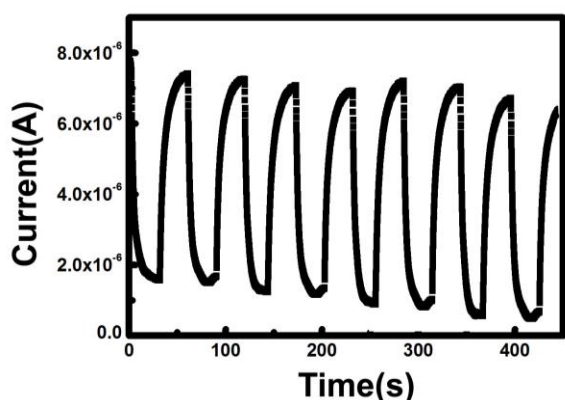


Fig. 5. The time-dependent response curve of the  $\text{Cu}_2\text{O}/\text{ZnO}$  heterojunction structures

#### 4. Discussion

For the  $\text{ZnO}/\text{Cu}_2\text{O}$  heterojunction structure, in dark conditions, oxygen molecules would adsorb on the  $\text{ZnO}$  nanosheets surface by capturing free electrons. It will create surface depletion layer with low conductivity. The density of electron-hole pairs in the  $\text{ZnO}$  nanosheets and  $\text{Cu}_2\text{O}$  film increases significantly when illuminated with UV light. The holes from the  $\text{Cu}_2\text{O}$  film excited by UV light would move to the  $\text{ZnO}$  nanosheet surface across the  $\text{ZnO}/\text{Cu}_2\text{O}$  heterojunction, then take part in the oxidation of the ionized oxygen and release one oxygen gas molecule by an electron-hole recombination process. Meanwhile, it is well known that one dimensional nanostructure can effectively improve the charge transport, but its low surface area limits the enhancement of photocurrent density. In our case,  $\text{Cu}_2\text{O}/\text{ZnO}$  nanosheets heterostructure could be one candidate which can simultaneously enhance surface area and charge transport. The high UV response can be attributed that large numbers of  $\text{ZnO}$  sheet-like structure with high surface-to-volume ratio on the  $\text{Cu}_2\text{O}$  film increased the surface area, and caused more active sites on the surface and high absorption in the UV region. Thus, the fabricated device showed excellent UV sensing properties.

#### 5. Conclusions

In summary, a highly sensitive UV sensor based on  $\text{Cu}_2\text{O}/\text{ZnO}$  nanosheets heterostructure was fabricated by using aqueous method. The heterostructure composed of  $\text{Cu}_2\text{O}$  film and  $\text{ZnO}$  nanosheet structure which exhibited a prominent performance for UV detection response. The results indicated the suitability of low-cost  $\text{ZnO}$  nanosheets/ $\text{Cu}_2\text{O}$  heterojunction device for optoelectronic applications. Furthermore, it will provide a facile route for large area growth  $\text{ZnO}$  nanosheets/ $\text{Cu}_2\text{O}$  for low cost UV detector applications.

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